

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

ECH8320 — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- · 1.8V drive
- · Halogen free compliance
- · Protection diode in

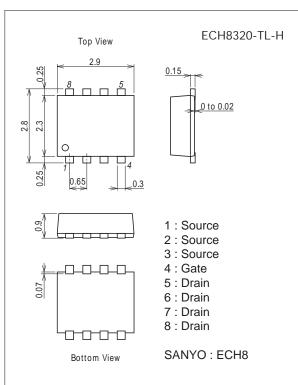
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	ID		-9.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-40	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7011A-002



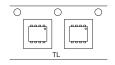
Product & Package Information

• Package : ECH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

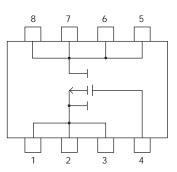
Packing Type: TL



Marking



Electrical Connection

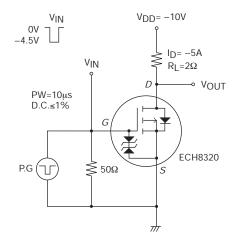


ECH8320

Electrical Characteristics at Ta=25°C

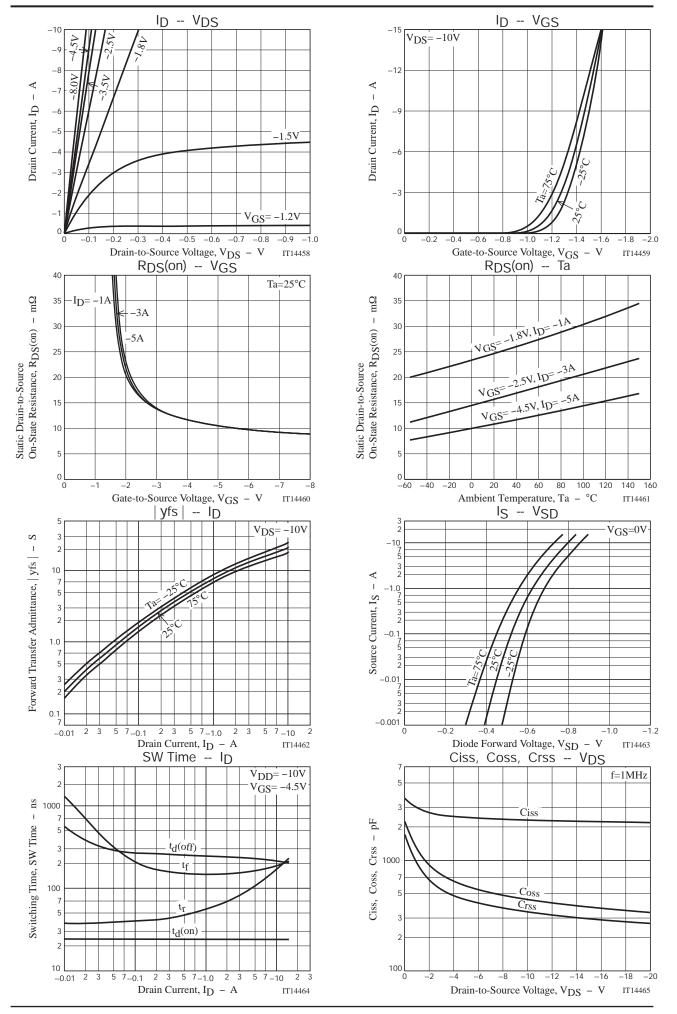
Parameter	Symbol	Conditions	Ratings			Unit
Parameter		Conditions	min	typ	max	Uniii
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-20V, V _{GS} =0V			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =-10V, I _D =-1mA	-0.4		-1.3	V
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-5A		16		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-5A, V _G S=-4.5V		11	14.5	mΩ
	R _{DS} (on)2	I _D =-3A, V _G S=-2.5V		16	23	mΩ
	R _{DS} (on)3	I _D =-1A, V _G S=-1.8V		25	39	mΩ
Input Capacitance	Ciss	V _{DS} =-10V, f=1MHz		2300		pF
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		440		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-10V, f=1MHz		340		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		24		ns
Rise Time	t _r	See specified Test Circuit.		100		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		230		ns
Fall Time	tf	See specified Test Circuit.		163		ns
Total Gate Charge	Qg	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-9.5A		25		nC
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-9.5A		3.6		nC
Gate-to-Drain "Miller" Charge	Qgd	V _D S=-10V, V _G S=-4.5V, I _D =-9.5A		7.6		nC
Diode Forward Voltage	V _{SD}	I _S =-9.5A, V _G S=0V		-0.79	-1.2	V

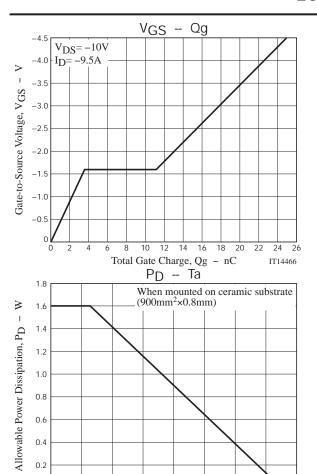
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo	
ECH8320-TL-H	ECH8320-TL-H ECH8		Pb Free and Halogen Free	





80

Ambient Temperature, Ta - °C

100

140

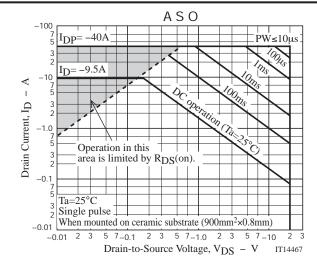
160

IT14468

0.2 0

0

20

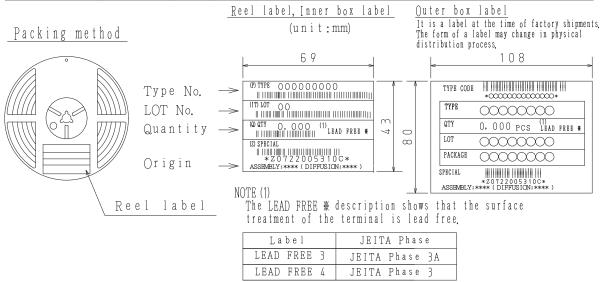


Embossed Taping Specification

ECH8320-TL-H

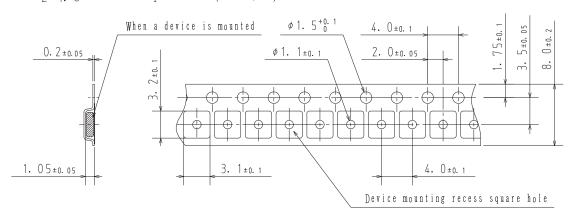
1. Packing Format

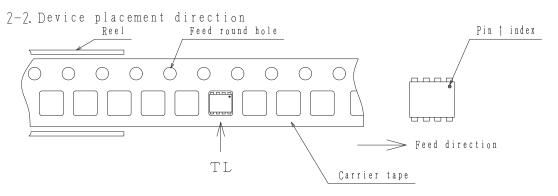
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	format
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained
					Dimensions:mm (external)	Dimensions:mm (external)
					183×72×185	440×195×210



2. Taping configuration

2-1. Carrier tape size (unit:mm)

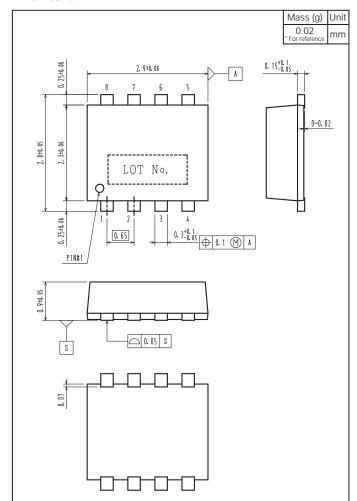




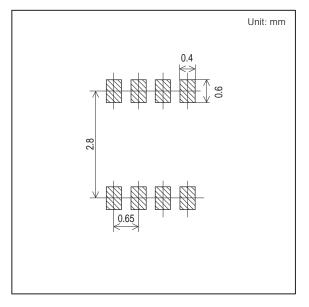
Those with pin 1 index on the feed hole side · · · · · TL

Outline Drawing

ECH8320-TL-H



Land Pattern Example



Note on usage: Since the ECH8320 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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